chip bonding type, said apparatus comprising:

a transparent base having a first surface;

first and a second bonding pads formed on said first surface;

a GaN semiconductor light-emitting device fixed on the first surface,

wherein a first lead frame includes a first mount which faces a dominant light emitting direction of the light-emitting apparatus and on which the first bonding pad is to be fixed, and a second lead frame includes a second mount which faces the dominant light emitting direction and on which the second bonding pad is to be fixed,

wherein the light-emitting device comprises a substrate, a light-emitting layer and a positive electrode comprising a light non-transmissible material, said positive electrode being disposed on an opposite side of said light-emitting layer from said substrate and reflecting light from said light-emitting layer in a direction through said substrate and said base.

21. (Thrice Amended) A light-emitting diode comprising:

a sapphire substrate:

a light emitting layer made of GaN semiconductor and formed on said sapphire substrate; and

a positive electrode and a negative electrode electrically coupled to said light emitting layer;

wherein said positive electrode and said negative electrode are supplied with electricity through a wire; and

wherein said positive electrode has a thickness of at least 300 Å, comprises a light non-transmissible material for reflecting light from said light emitting layer toward said sapphire substrate, and covers substantially an entire surface of the light-emitting layer.

Please add the following new claims:

- - 26. A semiconductor light-emitting apparatus comprising:

a base;

first and second bonding pads formed on a first surface of said base;

a light-emitting element formed between said first and second bonding pads on said first surface of said base, said light-emitting element comprising:

a substrate;

a light-emitting layer formed on said substrate; and

a first electrode disposed on an opposite side of said light-emitting layer from said base and reflecting light from said light-emitting layer through said base; and

a fluorescent material which is adjacent to said substrate and on an opposite side of said substrate from said light-emitting layer.

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27. The semiconductor light-emitting apparatus according to claim 26, further comprising:

first and second lead frames electrically connected to said first and second bonding pads, respectively.

28. The semiconductor light-emitting apparatus according to claim 27, wherein said light-emitting element further comprises a substrate disposed between said light-emitting layer and said base, and wherein said first electrode reflects light from said light-emitting layer through said substrate.

29. The semiconductor light-emitting apparatus according to claim 27, wherein a direction from said light-emitting layer toward said base comprises a dominant light-emitting direction.

30. The semiconductor light-emitting apparatus according to claim 29, wherein said first and second lead frames each comprise a projecting portion which reflects light in said dominant light-emitting direction.

31. The semiconductor light-emitting apparatus according to claim 27, wherein said first and second bonding pads are formed on said first surface of said base so as to maximize a

distance between said first and second lead frames.

32. The semiconductor light-emitting apparatus according to claim 26, wherein first and second bonding pads are formed on opposing outer edges of said first surface of said base.

33. The semiconductor light-emitting apparatus according to claim 26, wherein an adhesive adheres said light-emitting element to said first surface of said base.

34. The semiconductor light-emitting apparatus according to claim 26, wherein said light-emitting element further comprises a second electrode, said first and second electrodes being connected by bonding wires to said first and second bonding pads, respectively.

35. The semiconductor light-emitting apparatus according to claim 34, wherein said first and second lead frames and said bonding wires are connected to a same surface of said first and second bonding pads.

36. The semiconductor light-emitting apparatus according to claim 28, wherein said substrate of said light-emitting element is formed on said base.

37. The semiconductor light-emitting apparatus according to claim 14, further comprising:

a fluorescent material which is adjacent to said substrate and on an opposite side of said substrate from said light-emitting layer.

38. The pair of lead frames according to claim 19, wherein said apparatus further comprises a sealing resin formed over said transparent base and said GaN semiconductor light-emitting device. - -